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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	147456
Number of I/O	177
Number of Gates	1000000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m7a3p1000-2fg256

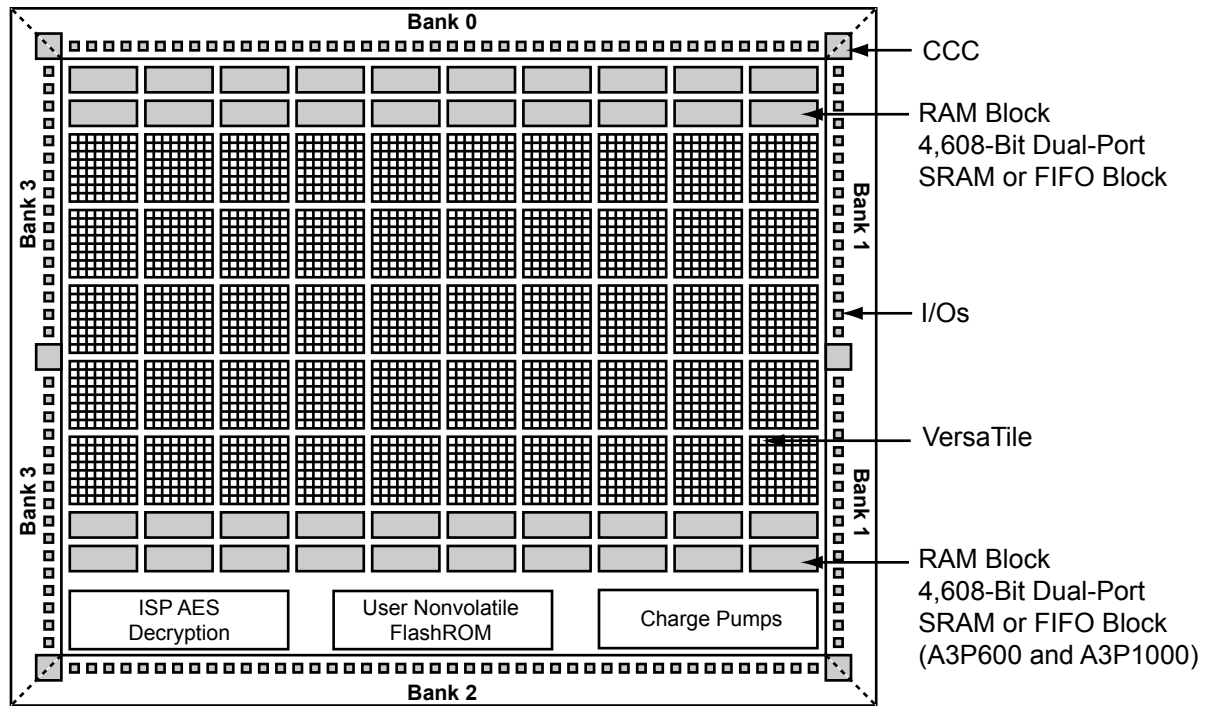


Figure 1-2 • ProASIC3 Device Architecture Overview with Four I/O Banks (A3P250, A3P600, and A3P1000)

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the ProASIC3 core tile as either a three-input lookup table (LUT) equivalent or as a D-flip-flop/latch with enable allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the Microsemi ProASIC family of third-generation architecture flash FPGAs. VersaTiles are connected with any of the four levels of routing hierarchy. Flash switches are distributed throughout the device to provide nonvolatile, reconfigurable interconnect programming. Maximum core utilization is possible for virtually any design.

VersaTiles

The ProASIC3 core consists of VersaTiles, which have been enhanced beyond the ProASIC^{PLUS}® core tiles. The ProASIC3 VersaTile supports the following:

- All 3-input logic functions—LUT-3 equivalent
- Latch with clear or set
- D-flip-flop with clear or set
- Enable D-flip-flop with clear or set

Refer to [Figure 1-3](#) for VersaTile configurations.

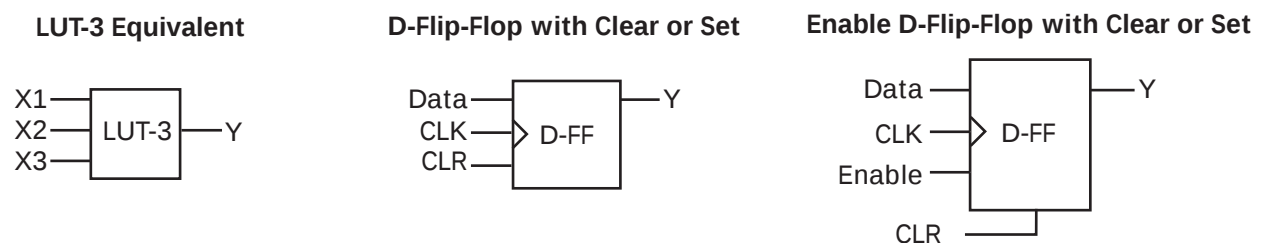


Figure 1-3 • VersaTile Configurations

Table 2-24 • Summary of I/O Timing Characteristics—Software Default Settings
 –2 Speed Grade, Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst Case $V_{CC} = 1.425\text{ V}$,
 Worst-Case V_{CCI} (per standard)
 Advanced I/O Banks

I/O Standard	Drive Strength	Equiv. Software Default Drive Strength Option ¹	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)	Units
3.3 V LVTTTL / 3.3 V LVCMOS	12 mA	12 mA	High	35	–	0.45	2.64	0.03	0.76	0.32	2.69	2.11	2.40	2.68	4.36	3.78	ns
3.3 V LVCMOS Wide Range ²	100 μA	12 mA	High	35	–	0.45	4.08	0.03	0.76	0.32	4.08	3.20	3.71	4.14	6.61	5.74	ns
2.5 V LVCMOS	12 mA	12 mA	High	35	–	0.45	2.66	0.03	0.98	0.32	2.71	2.56	2.47	2.57	4.38	4.23	ns
1.8 V LVCMOS	12 mA	12 mA	High	35	–	0.45	2.64	0.03	0.91	0.32	2.69	2.27	2.76	3.05	4.36	3.94	ns
1.5 V LVCMOS	12 mA	12 mA	High	35	–	0.45	3.05	0.03	1.07	0.32	3.10	2.67	2.95	3.14	4.77	4.34	ns
3.3 V PCI	Per PCI spec	–	High	10	25 ⁴	0.45	2.00	0.03	0.65	0.32	2.04	1.46	2.40	2.68	3.71	3.13	ns
3.3 V PCI-X	Per PCI-X spec	–	High	10	25 ⁴	0.45	2.00	0.03	0.62	0.32	2.04	1.46	2.40	2.68	3.71	3.13	ns
LVDS	24 mA	–	High	–	–	0.45	1.37	0.03	1.20	–	–	–	–	–	–	–	ns
LVPECL	24 mA	–	High	–	–	0.45	1.34	0.03	1.05	–	–	–	–	–	–	–	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.
4. Resistance is used to measure I/O propagation delays as defined in PCI specifications. See [Figure 2-11 on page 2-64](#) for connectivity. This resistor is not required during normal operation.

Table 2-33 • I/O Short Currents IOSH/IOSL
Applicable to Standard Plus I/O Banks

	Drive Strength	IOSL (mA) ¹	IOSH (mA) ¹
3.3 V LVTTTL / 3.3 V LVCMOS	2 mA	27	25
	4 mA	27	25
	6 mA	54	51
	8 mA	54	51
	12 mA	109	103
	16 mA	109	103
3.3 V LVCMOS Wide Range ²	100 μ A	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	18	16
	4 mA	18	16
	6 mA	37	32
	8 mA	37	32
	12 mA	74	65
1.8 V LVCMOS	2 mA	11	9
	4 mA	22	17
	6 mA	44	35
	8 mA	44	35
1.5 V LVCMOS	2 mA	16	13
	4 mA	33	25
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	109	103

Notes:

1. $T_J = 100^{\circ}\text{C}$
2. Applicable to 3.3 V LVCMOS Wide Range. IOSL/IOSH dependent on the I/O buffer drive strength selected for wide range applications. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.

Table 2-45 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew

 Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
	–2	0.49	3.29	0.03	0.75	0.32	3.36	2.80	1.79	2.01	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-46 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew

 Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.66	9.46	0.04	1.00	0.43	9.64	8.54	2.07	2.04	ns
	–1	0.56	8.05	0.04	0.85	0.36	8.20	7.27	1.76	1.73	ns
	–2	0.49	7.07	0.03	0.75	0.32	7.20	6.38	1.55	1.52	ns
4 mA	Std.	0.66	9.46	0.04	1.00	0.43	9.64	8.54	2.07	2.04	ns
	–1	0.56	8.05	0.04	0.85	0.36	8.20	7.27	1.76	1.73	ns
	–2	0.49	7.07	0.03	0.75	0.32	7.20	6.38	1.55	1.52	ns
6 mA	Std.	0.66	6.57	0.04	1.00	0.43	6.69	5.98	2.40	2.57	ns
	–1	0.56	5.59	0.04	0.85	0.36	5.69	5.09	2.04	2.19	ns
	–2	0.49	4.91	0.03	0.75	0.32	5.00	4.47	1.79	1.92	ns
8 mA	Std.	0.66	6.57	0.04	1.00	0.43	6.69	5.98	2.40	2.57	ns
	–1	0.56	5.59	0.04	0.85	0.36	5.69	5.09	2.04	2.19	ns
	–2	0.49	4.91	0.03	0.75	0.32	5.00	4.47	1.79	1.92	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-49 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard I/O Banks

3.3 V LVCMOS Wide Range	Equiv. Software Default	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ²	IIH ³
Drive Strength	Drive Strength Option ¹	Min V	Max V	Min V	Max V	Max V	Min V	μA	μA	Max mA ⁴	Max mA ⁴	μA ⁵	μA ⁵
100 μA	2 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	25	27	10	10
100 μA	4 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	25	27	10	10
100 μA	6 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	51	54	10	10
100 μA	8 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	51	54	10	10

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 μA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. IIL is the input leakage current per I/O pin over recommended operation conditions where −0.3 V < VIN < VIL.
3. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges
4. Currents are measured at 85°C junction temperature.
5. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.
6. Software default selection highlighted in gray.

Table 2-61 • 2.5 V LVCMOS Low Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$
 Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.60	11.40	0.04	1.31	0.43	11.22	11.40	2.68	2.20	13.45	13.63	ns
	–1	0.51	9.69	0.04	1.11	0.36	9.54	9.69	2.28	1.88	11.44	11.60	ns
	–2	0.45	8.51	0.03	0.98	0.32	8.38	8.51	2.00	1.65	10.05	10.18	ns
6 mA	Std.	0.60	7.96	0.04	1.31	0.43	8.11	7.81	3.05	2.89	10.34	10.05	ns
	–1	0.51	6.77	0.04	1.11	0.36	6.90	6.65	2.59	2.46	8.80	8.55	ns
	–2	0.45	5.94	0.03	0.98	0.32	6.05	5.84	2.28	2.16	7.72	7.50	ns
8 mA	Std.	0.60	7.96	0.04	1.31	0.43	8.11	7.81	3.05	2.89	10.34	10.05	ns
	–1	0.51	6.77	0.04	1.11	0.36	6.90	6.65	2.59	2.46	8.80	8.55	ns
	–2	0.45	5.94	0.03	0.98	0.32	6.05	5.84	2.28	2.16	7.72	7.50	ns
12 mA	Std.	0.60	6.18	0.04	1.31	0.43	6.29	5.92	3.30	3.32	8.53	8.15	ns
	–1	0.51	5.26	0.04	1.11	0.36	5.35	5.03	2.81	2.83	7.26	6.94	ns
	–2	0.45	4.61	0.03	0.98	0.32	4.70	4.42	2.47	2.48	6.37	6.09	ns
16 mA	Std.	0.60	5.76	0.04	1.31	0.43	5.87	5.53	3.36	3.44	8.11	7.76	ns
	–1	0.51	4.90	0.04	1.11	0.36	4.99	4.70	2.86	2.92	6.90	6.60	ns
	–2	0.45	4.30	0.03	0.98	0.32	4.38	4.13	2.51	2.57	6.05	5.80	ns
24 mA	Std.	0.60	5.51	0.04	1.31	0.43	5.50	5.51	3.43	3.87	7.74	7.74	ns
	–1	0.51	4.68	0.04	1.11	0.36	4.68	4.68	2.92	3.29	6.58	6.59	ns
	–2	0.45	4.11	0.03	0.98	0.32	4.11	4.11	2.56	2.89	5.78	5.78	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-72 • 1.8 V LVC MOS High Slew**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.7\text{ V}$** **Applicable to Standard Plus I/O Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	11.33	0.04	1.20	0.43	8.72	11.33	2.24	1.52	10.96	13.57	ns
	–1	0.56	9.64	0.04	1.02	0.36	7.42	9.64	1.91	1.29	9.32	11.54	ns
	–2	0.49	8.46	0.03	0.90	0.32	6.51	8.46	1.68	1.14	8.18	10.13	ns
4 mA	Std.	0.66	6.48	0.04	1.20	0.43	5.48	6.48	2.65	2.60	7.72	8.72	ns
	–1	0.56	5.51	0.04	1.02	0.36	4.66	5.51	2.25	2.21	6.56	7.42	ns
	–2	0.49	4.84	0.03	0.90	0.32	4.09	4.84	1.98	1.94	5.76	6.51	ns
6 mA	Std.	0.66	4.06	0.04	1.20	0.43	3.84	4.06	2.93	3.10	6.07	6.30	ns
	–1	0.56	3.45	0.04	1.02	0.36	3.27	3.45	2.49	2.64	5.17	5.36	ns
	–2	0.49	3.03	0.03	0.90	0.32	2.87	3.03	2.19	2.32	4.54	4.70	ns
8 mA	Std.	0.66	4.06	0.04	1.20	0.43	3.84	4.06	2.93	3.10	6.07	6.30	ns
	–1	0.56	3.45	0.04	1.02	0.36	3.27	3.45	2.49	2.64	5.17	5.36	ns
	–2	0.49	3.03	0.03	0.90	0.32	2.87	3.03	2.19	2.32	4.54	4.70	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-73 • 1.8 V LVC MOS Low Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.7\text{ V}$
 Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	14.80	0.04	1.20	0.43	13.49	14.80	2.25	1.46	15.73	17.04	ns
	–1	0.56	12.59	0.04	1.02	0.36	11.48	12.59	1.91	1.25	13.38	14.49	ns
	–2	0.49	11.05	0.03	0.90	0.32	10.08	11.05	1.68	1.09	11.75	12.72	ns
4 mA	Std.	0.66	9.90	0.04	1.20	0.43	9.73	9.90	2.65	2.50	11.97	12.13	ns
	–1	0.56	8.42	0.04	1.02	0.36	8.28	8.42	2.26	2.12	10.18	10.32	ns
	–2	0.49	7.39	0.03	0.90	0.32	7.27	7.39	1.98	1.86	8.94	9.06	ns
6 mA	Std.	0.66	7.44	0.04	1.20	0.43	7.58	7.32	2.94	2.99	9.81	9.56	ns
	–1	0.56	6.33	0.04	1.02	0.36	6.44	6.23	2.50	2.54	8.35	8.13	ns
	–2	0.49	5.55	0.03	0.90	0.32	5.66	5.47	2.19	2.23	7.33	7.14	ns
8 mA	Std.	0.66	7.44	0.04	1.20	0.43	7.58	7.32	2.94	2.99	9.81	9.56	ns
	–1	0.56	6.33	0.04	1.02	0.36	6.44	6.23	2.50	2.54	8.35	8.13	ns
	–2	0.49	5.55	0.03	0.90	0.32	5.66	5.47	2.19	2.23	7.33	7.14	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-74 • 1.8 V LVC MOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.7\text{ V}$
 Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.66	11.21	0.04	1.20	0.43	8.53	11.21	1.99	1.21	ns
	–1	0.56	9.54	0.04	1.02	0.36	7.26	9.54	1.69	1.03	ns
	–2	0.49	8.37	0.03	0.90	0.32	6.37	8.37	1.49	0.90	ns
4 mA	Std.	0.66	6.34	0.04	1.20	0.43	5.38	6.34	2.41	2.48	ns
	–1	0.56	5.40	0.04	1.02	0.36	4.58	5.40	2.05	2.11	ns
	–2	0.49	4.74	0.03	0.90	0.32	4.02	4.74	1.80	1.85	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-97 • Parameter Definition and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OSUE}	Enable Setup Time for the Output Data Register	GG, HH
t_{OHE}	Enable Hold Time for the Output Data Register	GG, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
t_{OESUE}	Enable Setup Time for the Output Enable Register	KK, HH
t_{OEHE}	Enable Hold Time for the Output Enable Register	KK, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ISUE}	Enable Setup Time for the Input Data Register	BB, AA
t_{IHE}	Enable Hold Time for the Input Data Register	BB, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

Note: *See Figure 2-16 on page 2-71 for more information.

Output Enable Register

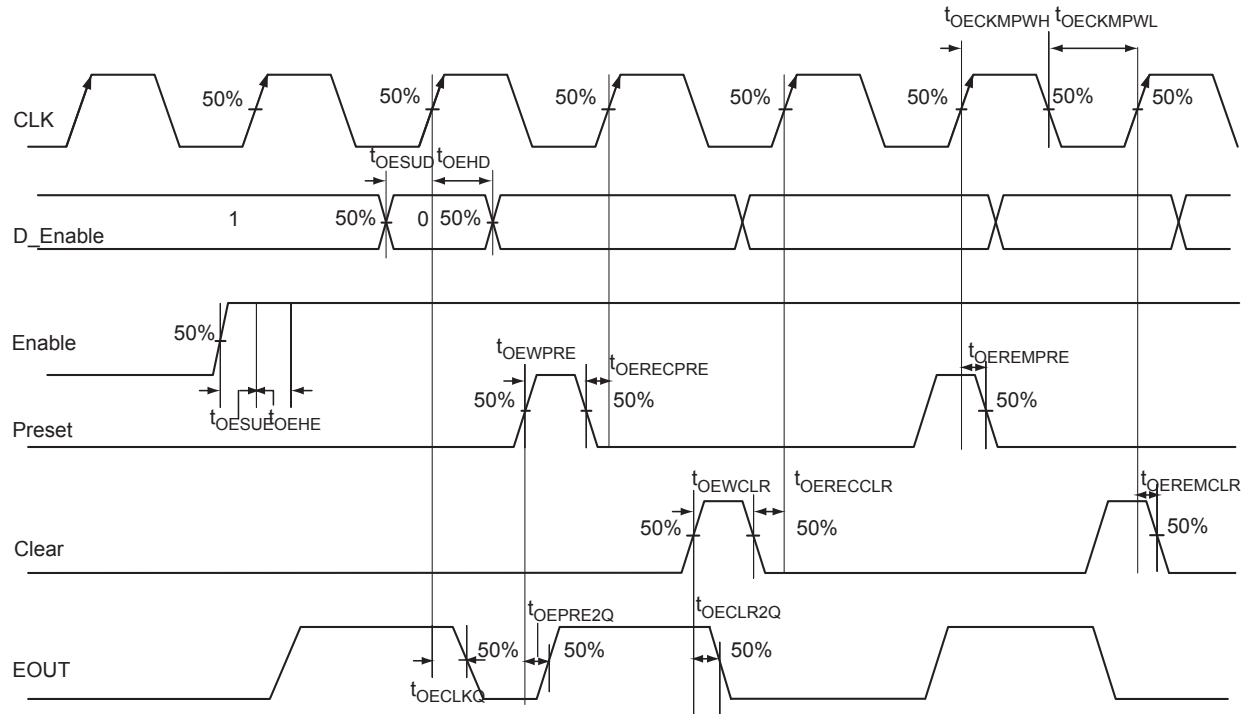


Figure 2-19 • Output Enable Register Timing Diagram

VersaTile Characteristics

VersaTile Specifications as a Combinatorial Module

The ProASIC3 library offers all combinations of LUT-3 combinatorial functions. In this section, timing characteristics are presented for a sample of the library. For more details, refer to the [Fusion](#), [IGLOO®/e](#), and [ProASIC3/E Macro Library Guide](#).

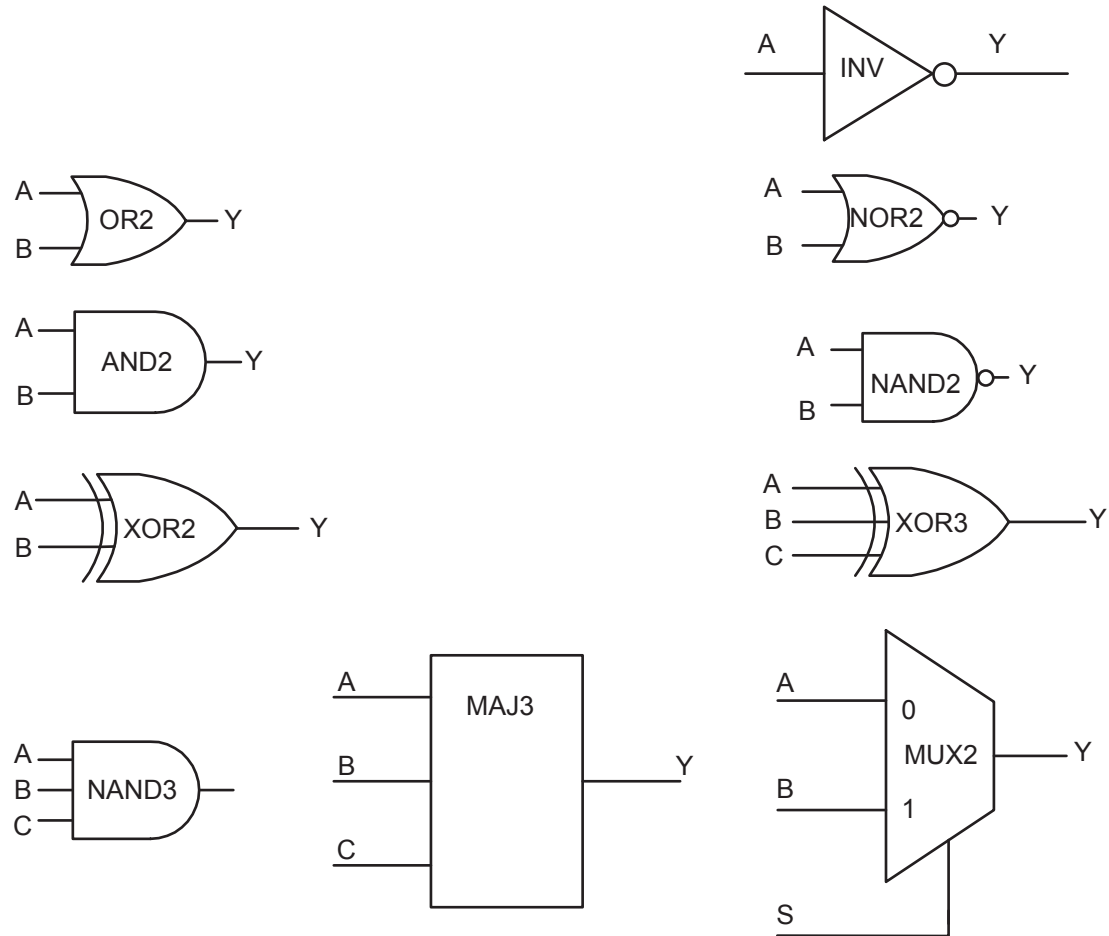


Figure 2-24 • Sample of Combinatorial Cells

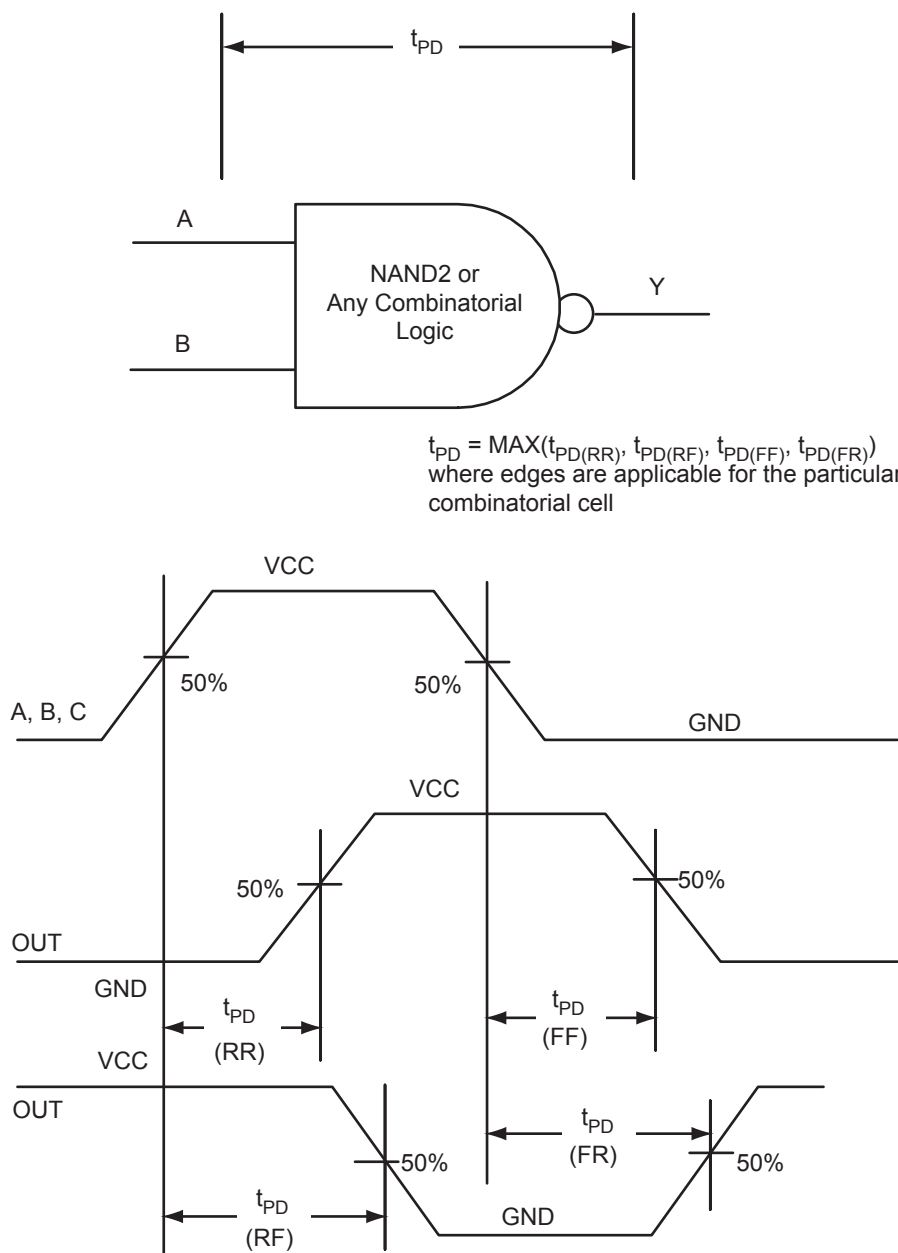


Figure 2-25 • Timing Model and Waveforms

Global Resource Characteristics

A3P250 Clock Tree Topology

Clock delays are device-specific. [Figure 2-28](#) is an example of a global tree used for clock routing. The global tree presented in [Figure 2-28](#) is driven by a CCC located on the west side of the A3P250 device. It is used to drive all D-flip-flops in the device.

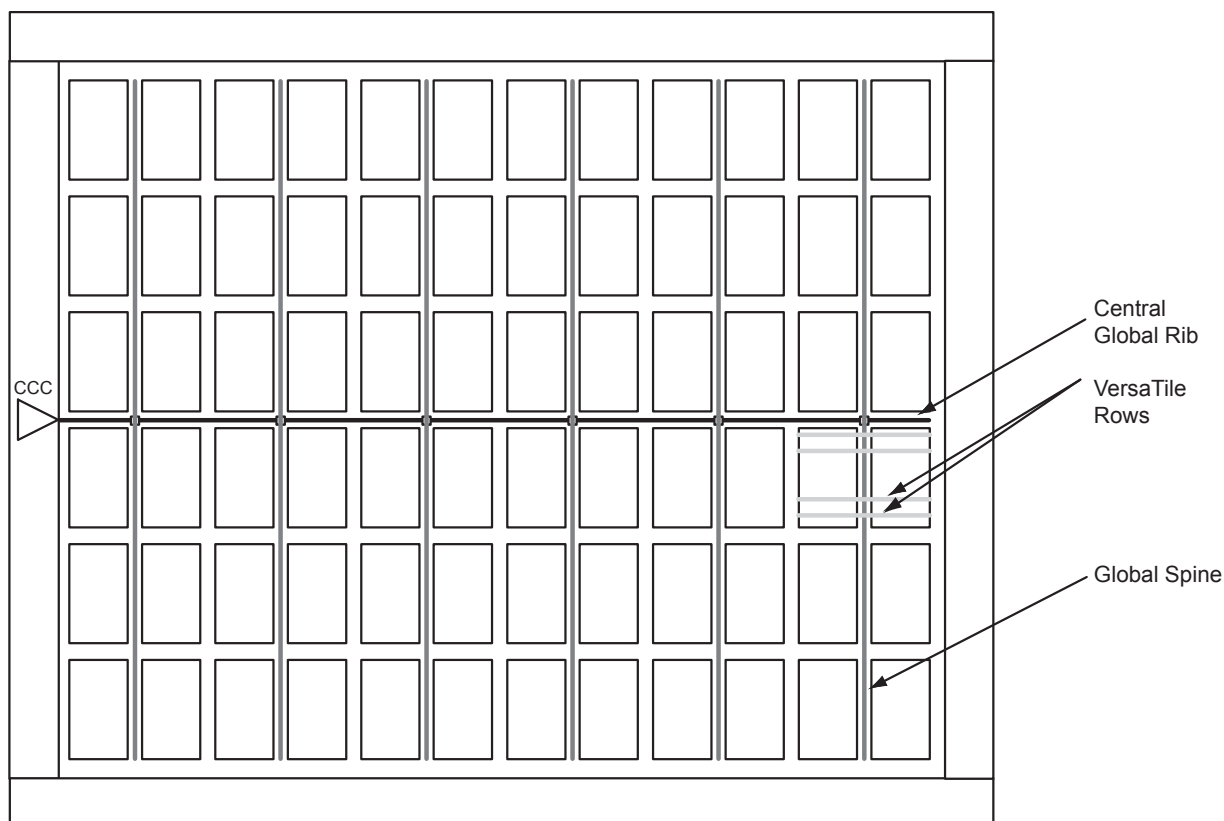


Figure 2-28 • Example of Global Tree Use in an A3P250 Device for Clock Routing

Global Tree Timing Characteristics

Global clock delays include the central rib delay, the spine delay, and the row delay. Delays do not include I/O input buffer clock delays, as these are I/O standard-dependent, and the clock may be driven and conditioned internally by the CCC module. For more details on clock conditioning capabilities, refer to the ["Clock Conditioning Circuits" section on page 2-90](#). [Table 2-108](#) to [Table 2-114 on page 2-89](#) present minimum and maximum global clock delays within each device. Minimum and maximum delays are measured with minimum and maximum loading.

Table 2-109 • A3P060 Global Resource
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2		-1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.71	0.93	0.81	1.05	0.95	1.24	ns
t_{RCKH}	Input High Delay for Global Clock	0.70	0.96	0.80	1.09	0.94	1.28	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.26		0.29		0.34	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-110 • A3P125 Global Resource
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2		-1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.77	0.99	0.87	1.12	1.03	1.32	ns
t_{RCKH}	Input High Delay for Global Clock	0.76	1.02	0.87	1.16	1.02	1.37	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.26		0.29		0.34	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

FIFO

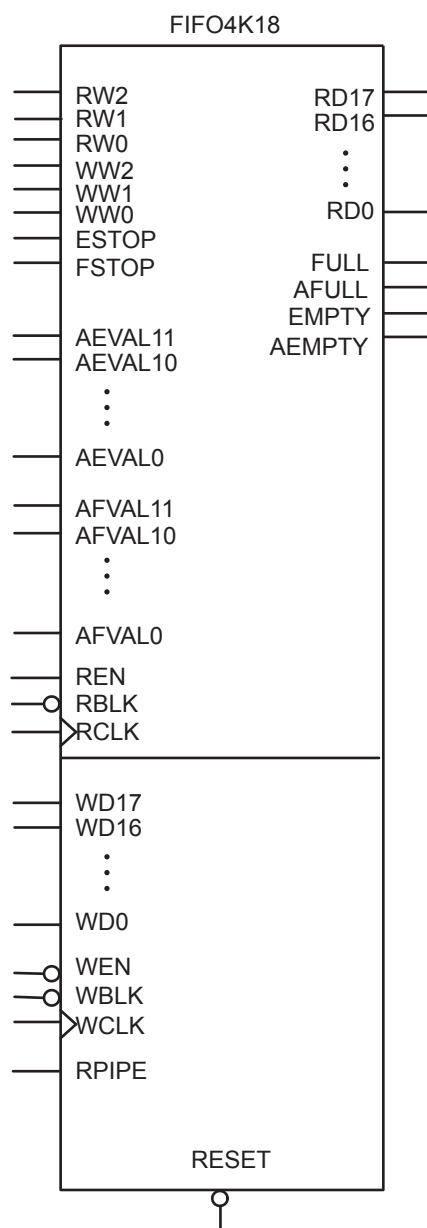
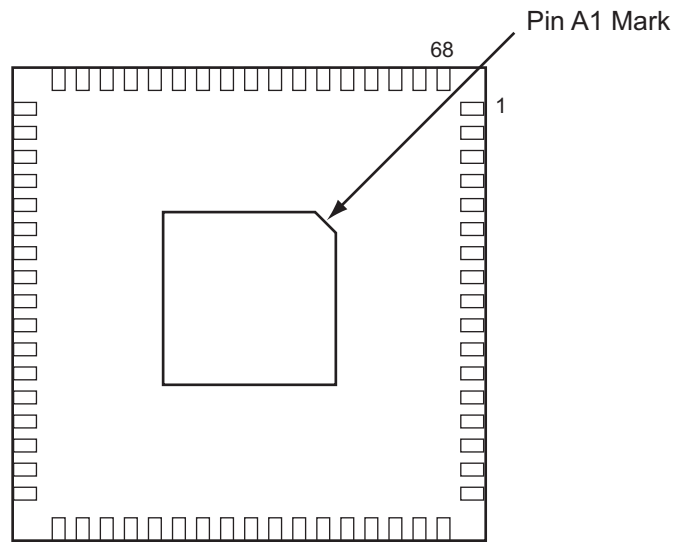


Figure 2-36 • FIFO Model

QN68 – Bottom View



Note: The die attach paddle center of the package is tied to ground (GND).

Note

For more information on package drawings, see [PD3068: Package Mechanical Drawings](#).

QN68	
Pin Number	A3P030 Function
1	IO82RSB1
2	IO80RSB1
3	IO78RSB1
4	IO76RSB1
5	GEC0/IO73RSB1
6	GEA0/IO72RSB1
7	GEB0/IO71RSB1
8	VCC
9	GND
10	VCCIB1
11	IO68RSB1
12	IO67RSB1
13	IO66RSB1
14	IO65RSB1
15	IO64RSB1
16	IO63RSB1
17	IO62RSB1
18	IO60RSB1
19	IO58RSB1
20	IO56RSB1
21	IO54RSB1
22	IO52RSB1
23	IO51RSB1
24	VCC
25	GND
26	VCCIB1
27	IO50RSB1
28	IO48RSB1
29	IO46RSB1
30	IO44RSB1
31	IO42RSB1
32	TCK
33	TDI
34	TMS
35	VPUMP
36	TDO

QN68	
Pin Number	A3P030 Function
37	TRST
38	VJTAG
39	IO40RSB0
40	IO37RSB0
41	GDB0/IO34RSB0
42	GDA0/IO33RSB0
43	GDC0/IO32RSB0
44	VCCIB0
45	GND
46	VCC
47	IO31RSB0
48	IO29RSB0
49	IO28RSB0
50	IO27RSB0
51	IO25RSB0
52	IO24RSB0
53	IO22RSB0
54	IO21RSB0
55	IO19RSB0
56	IO17RSB0
57	IO15RSB0
58	IO14RSB0
59	VCCIB0
60	GND
61	VCC
62	IO12RSB0
63	IO10RSB0
64	IO08RSB0
65	IO06RSB0
66	IO04RSB0
67	IO02RSB0
68	IO00RSB0

TQ144	
Pin Number	A3P060 Function
1	GAA2/IO51RSB1
2	IO52RSB1
3	GAB2/IO53RSB1
4	IO95RSB1
5	GAC2/IO94RSB1
6	IO93RSB1
7	IO92RSB1
8	IO91RSB1
9	VCC
10	GND
11	VCCIB1
12	IO90RSB1
13	GFC1/IO89RSB1
14	GFC0/IO88RSB1
15	GFB1/IO87RSB1
16	GFB0/IO86RSB1
17	VCOMPLF
18	GFA0/IO85RSB1
19	VCCPLF
20	GFA1/IO84RSB1
21	GFA2/IO83RSB1
22	GFB2/IO82RSB1
23	GFC2/IO81RSB1
24	IO80RSB1
25	IO79RSB1
26	IO78RSB1
27	GND
28	VCCIB1
29	GEC1/IO77RSB1
30	GEC0/IO76RSB1
31	GEB1/IO75RSB1
32	GEB0/IO74RSB1
33	GEA1/IO73RSB1
34	GEA0/IO72RSB1
35	VMV1
36	GNDQ

TQ144	
Pin Number	A3P060 Function
37	NC
38	GEA2/IO71RSB1
39	GEB2/IO70RSB1
40	GEC2/IO69RSB1
41	IO68RSB1
42	IO67RSB1
43	IO66RSB1
44	IO65RSB1
45	VCC
46	GND
47	VCCIB1
48	NC
49	IO64RSB1
50	NC
51	IO63RSB1
52	NC
53	IO62RSB1
54	NC
55	IO61RSB1
56	NC
57	NC
58	IO60RSB1
59	IO59RSB1
60	IO58RSB1
61	IO57RSB1
62	NC
63	GND
64	NC
65	GDC2/IO56RSB1
66	GDB2/IO55RSB1
67	GDA2/IO54RSB1
68	GNDQ
69	TCK
70	TDI
71	TMS
72	VMV1

TQ144	
Pin Number	A3P060 Function
73	VPUMP
74	NC
75	TDO
76	TRST
77	VJTAG
78	GDA0/IO50RSB0
79	GDB0/IO48RSB0
80	GDB1/IO47RSB0
81	VCCIB0
82	GND
83	IO44RSB0
84	GCC2/IO43RSB0
85	GCB2/IO42RSB0
86	GCA2/IO41RSB0
87	GCA0/IO40RSB0
88	GCA1/IO39RSB0
89	GCB0/IO38RSB0
90	GCB1/IO37RSB0
91	GCC0/IO36RSB0
92	GCC1/IO35RSB0
93	IO34RSB0
94	IO33RSB0
95	NC
96	NC
97	NC
98	VCCIB0
99	GND
100	VCC
101	IO30RSB0
102	GBC2/IO29RSB0
103	IO28RSB0
104	GBB2/IO27RSB0
105	IO26RSB0
106	GBA2/IO25RSB0
107	VMV0
108	GNDQ

PQ208	
Pin Number	A3P1000 Function
109	TRST
110	VJTAG
111	GDA0/IO113NDB1
112	GDA1/IO113PDB1
113	GDB0/IO112NDB1
114	GDB1/IO112PDB1
115	GDC0/IO111NDB1
116	GDC1/IO111PDB1
117	IO109NDB1
118	IO109PDB1
119	IO106NDB1
120	IO106PDB1
121	IO104PSB1
122	GND
123	VCCIB1
124	IO99NDB1
125	IO99PDB1
126	NC
127	IO96NDB1
128	GCC2/IO96PDB1
129	GCB2/IO95PSB1
130	GND
131	GCA2/IO94PSB1
132	GCA1/IO93PDB1
133	GCA0/IO93NDB1
134	GCB0/IO92NDB1
135	GCB1/IO92PDB1
136	GCC0/IO91NDB1
137	GCC1/IO91PDB1
138	IO88NDB1
139	IO88PDB1
140	VCCIB1
141	GND
142	VCC
143	IO86PSB1
144	IO84NDB1

PQ208	
Pin Number	A3P1000 Function
145	IO84PDB1
146	IO82NDB1
147	IO82PDB1
148	IO80NDB1
149	GBC2/IO80PDB1
150	IO79NDB1
151	GBB2/IO79PDB1
152	IO78NDB1
153	GBA2/IO78PDB1
154	VMV1
155	GNDQ
156	GND
157	VMV0
158	GBA1/IO77RSB0
159	GBA0/IO76RSB0
160	GBB1/IO75RSB0
161	GBB0/IO74RSB0
162	GND
163	GBC1/IO73RSB0
164	GBC0/IO72RSB0
165	IO70RSB0
166	IO67RSB0
167	IO63RSB0
168	IO60RSB0
169	IO57RSB0
170	VCCIB0
171	VCC
172	IO54RSB0
173	IO51RSB0
174	IO48RSB0
175	IO45RSB0
176	IO42RSB0
177	IO40RSB0
178	GND
179	IO38RSB0
180	IO35RSB0

PQ208	
Pin Number	A3P1000 Function
181	IO33RSB0
182	IO31RSB0
183	IO29RSB0
184	IO27RSB0
185	IO25RSB0
186	VCCIB0
187	VCC
188	IO22RSB0
189	IO20RSB0
190	IO18RSB0
191	IO16RSB0
192	IO15RSB0
193	IO14RSB0
194	IO13RSB0
195	GND
196	IO12RSB0
197	IO11RSB0
198	IO10RSB0
199	IO09RSB0
200	VCCIB0
201	GAC1/IO05RSB0
202	GAC0/IO04RSB0
203	GAB1/IO03RSB0
204	GAB0/IO02RSB0
205	GAA1/IO01RSB0
206	GAA0/IO00RSB0
207	GNDQ
208	VMV0

Datasheet Categories

Categories

In order to provide the latest information to designers, some datasheet parameters are published before data has been fully characterized from silicon devices. The data provided for a given device, as highlighted in the "ProASIC3 Device Status" table on page IV, is designated as either "Product Brief," "Advance," "Preliminary," or "Production." The definitions of these categories are as follows:

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The product brief is a summarized version of a datasheet (advance or production) and contains general product information. This document gives an overview of specific device and family information.

Advance

This version contains initial estimated information based on simulation, other products, devices, or speed grades. This information can be used as estimates, but not for production. This label only applies to the DC and Switching Characteristics chapter of the datasheet and will only be used when the data has not been fully characterized.

Preliminary

The datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.

Unmarked (production)

This version contains information that is considered to be final.

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